

IGBT - Power, Single, N-Channel, Field Stop VII (FS7), SCR, Power TO247-4L 1200 V, 1.4 V, 40 A

AFGH4L40T120RW

Description

Using the novel field stop 7th generation IGBT technology in TO247 4-lead package, this device offers the optimum performance with low on state voltage and minimal switching losses for both hard and soft switching topologies in automotive applications.

Features

- Extremely Efficient Trench with Field Stop Technology
- Maximum Junction Temperature – $T_J = 175^\circ\text{C}$
- Short Circuit Rated and Low Saturation Voltage
- Fast Switching and Tightened Parameter Distribution
- AEC-Q101 Qualified, PPAP Available Upon Request
- These Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

Applications

- Automotive E-compressor
- Automotive EV PTC Heater
- OBC

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

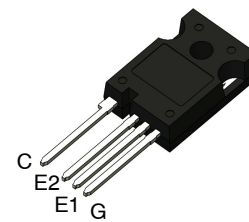
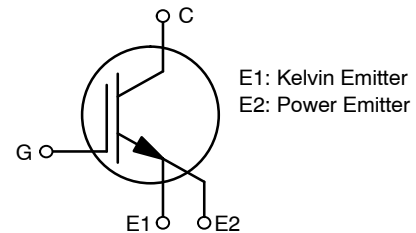
Parameter	Symbol	Value	Unit
Collector to Emitter Voltage	V_{CE}	1200	V
Gate to Emitter Voltage	V_{GE}	± 20	V
Transient Gate to Emitter Voltage		± 30	
Collector Current	I_C	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
Power Dissipation	P_D	$T_C = 25^\circ\text{C}$	W
		$T_C = 100^\circ\text{C}$	
Pulsed Collector Current	I_{CM}	120	A
Short Circuit Withstand Time $V_{GE} = 15\text{ V}, V_{CC} = 800\text{ V}, T_C = 150^\circ\text{C}$	T_{SC}	6	μs
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$
Lead Temperature for Soldering Purposes	T_L	260	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating; Pulse width limited by max. junction temperature

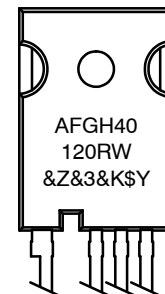
BV_{CES}	$V_{CE(sat)}$ TYP	I_C MAX
1200 V	1.4 V	40 A

PIN CONNECTIONS



TO-247-4LD
CASE 340CJ

MARKING DIAGRAM



AFGH40120RW = Specific Device Code
&Z = Assembly Plant Code
&3 = 3-Digit Date Code
&K = 2-Digit Lot Traceability Code
\$Y = onsemi Logo

ORDERING INFORMATION

Device	Package	Shipping
AFGH4L40T120RW	TO-247-4L (Pb-Free)	30 Units / Rail

AFGH4L40T120RW

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case for IGBT	$R_{\theta JC}$	0.26	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector to Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	1200	–	–	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	–	–	40	μA
Gate-to-Emitter leakage Current	I_{GES}	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0\text{ V}$	–	–	± 400	nA

ON CHARACTERISTICS

Gate to Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 40\text{ mA}, T_J = 25^\circ\text{C}$	5.03	5.93	6.83	V
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 25^\circ\text{C}$	–	1.4	1.73	V
		$V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 175^\circ\text{C}$	–	1.66	–	

DYNAMIC CHARACTERISTICS

Input Capacitance	C_{IES}	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	–	4721	–	pF
Output Capacitance	C_{OES}		–	144	–	pF
Reverse Transfer Capacitance	C_{RES}		–	24.2	–	pF
Total Gate Charge	Q_G	$V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}, I_C = 40\text{ A}$	–	171	–	nC
Gate to Emitter Charge	Q_{GE}		–	42.2	–	nC
Gate to Collector Charge	Q_{GC}		–	73.4	–	nC

SWITCHING CHARACTERISTICS, INDUCTIVE LOAD (Note: Si Diode Applied)

Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}$ $V_{GE} = 0/15\text{ V}$ $I_C = 20\text{ A}$ $R_G = 6\ \Omega$ $T_J = 25^\circ\text{C}$	–	53.5	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	311	–	
Rise Time	t_r		–	27.8	–	
Fall Time	t_f		–	189	–	mJ
Turn-On Switching Loss	E_{on}		–	1.26	–	
Turn-Off Switching Loss	E_{off}		–	1.36	–	
Total Switching Loss	E_{ts}		–	2.61	–	
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}$ $V_{GE} = 0/15\text{ V}$ $I_C = 40\text{ A}$ $R_G = 6\ \Omega$ $T_J = 25^\circ\text{C}$	–	58.2	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	258	–	
Rise time	t_r		–	47.4	–	
Fall Time	t_f		–	122	–	mJ
Turn-On Switching Loss	E_{on}		–	3.38	–	
Turn-Off Switching Loss	E_{off}		–	1.7	–	
Total Switching Loss	E_{ts}		–	5.08	–	

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS, INDUCTIVE LOAD (Note: Si Diode Applied)						
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}$ $V_{GE} = 0/15\text{ V}$ $I_C = 20\text{ A}$ $R_G = 6\ \Omega$ $T_J = 175^\circ\text{C}$	–	58.7	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	433	–	
Rise Time	t_r		–	39.4	–	
Fall Time	t_f		–	376	–	
Turn-On Switching Loss	E_{on}		–	2.01	–	mJ
Turn-Off Switching Loss	E_{off}		–	2.52	–	
Total Switching Loss	E_{ts}		–	4.53	–	
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}$ $V_{GE} = 0/15\text{ V}$ $I_C = 40\text{ A}$ $R_G = 6\ \Omega$ $T_J = 175^\circ\text{C}$	–	65.7	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	343	–	
Rise Time	t_r		–	64.7	–	
Fall Time	t_f		–	233	–	
Turn-On Switching Loss	E_{on}		–	5.45	–	mJ
Turn-Off Switching Loss	E_{off}		–	3.04	–	
Total Switching Loss	E_{ts}		–	8.49	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

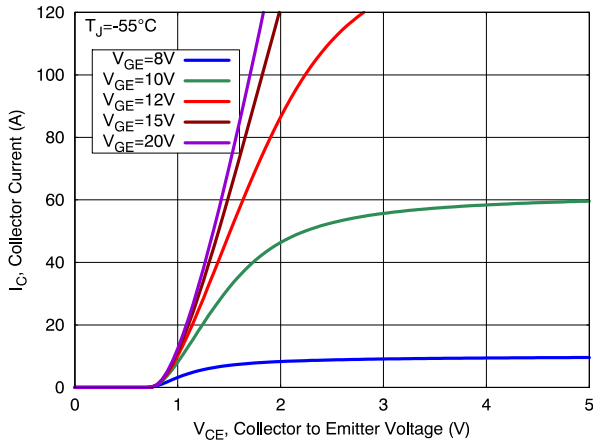


Figure 1. Output Characteristics

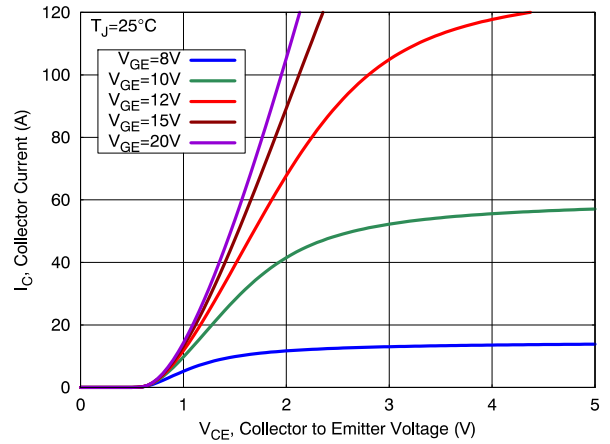


Figure 2. Output Characteristics

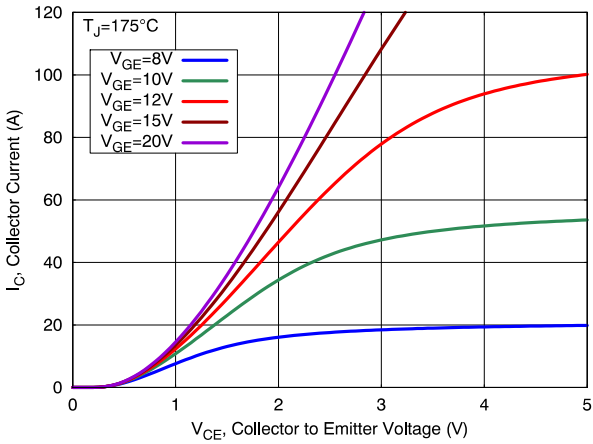


Figure 3. Output Characteristics

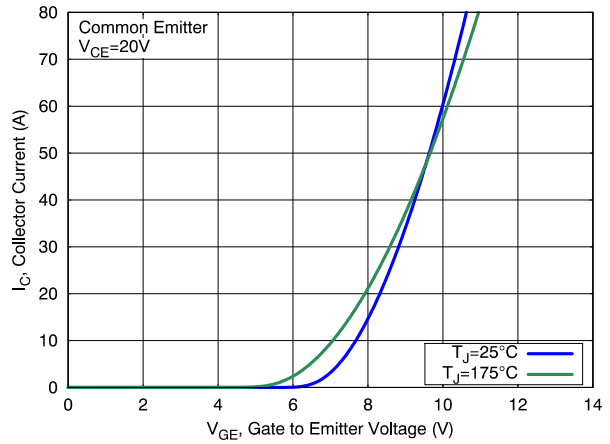


Figure 4. Transfer Characteristics

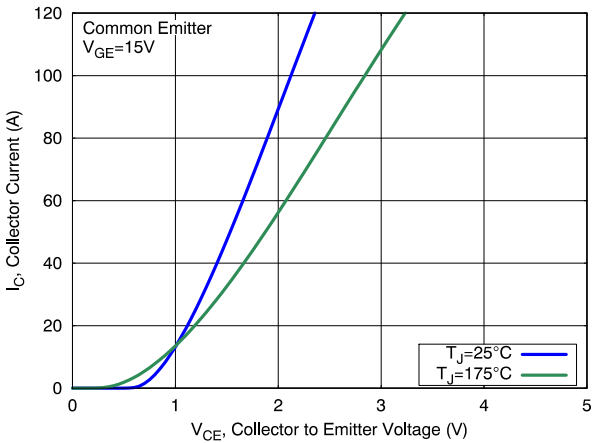


Figure 5. Saturation Characteristics

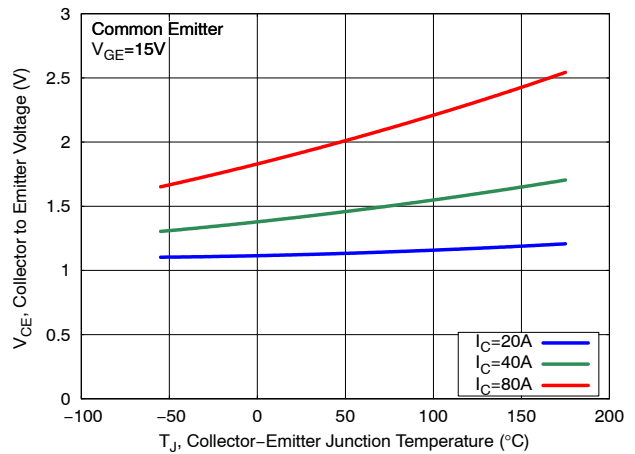


Figure 6. Saturation Voltage vs. Junction Temperature

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TYPICAL CHARACTERISTICS

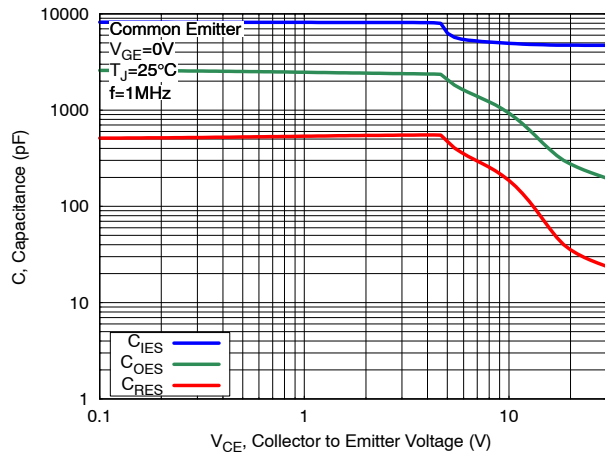


Figure 7. Capacitance Characteristics

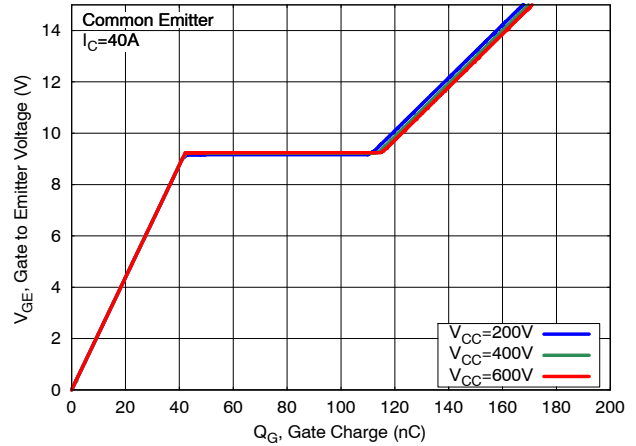


Figure 8. Gate Charge Characteristics

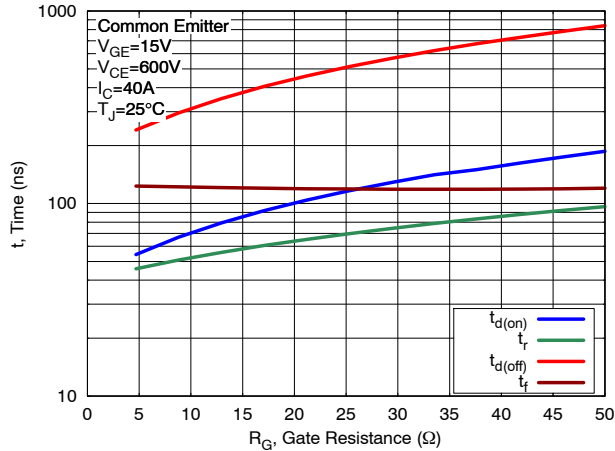


Figure 9. Switching Time vs Gate Resistance

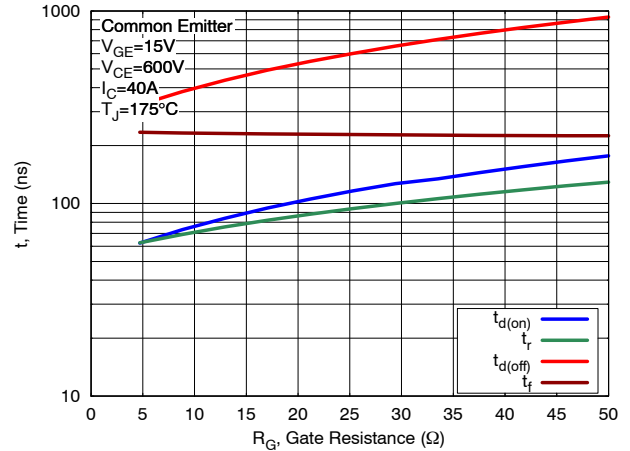


Figure 10. Switching Time vs Gate Resistance

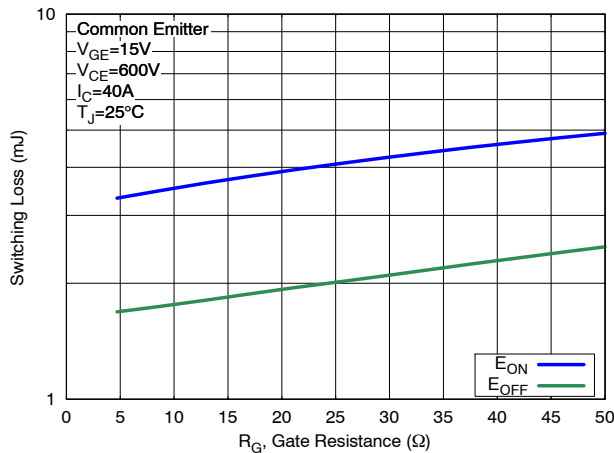


Figure 11. Switching Loss vs Gate Resistance

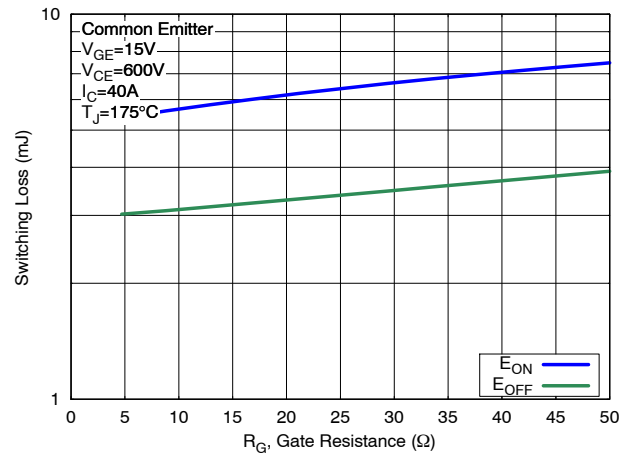


Figure 12. Switching Loss vs Gate Resistance

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TYPICAL CHARACTERISTICS

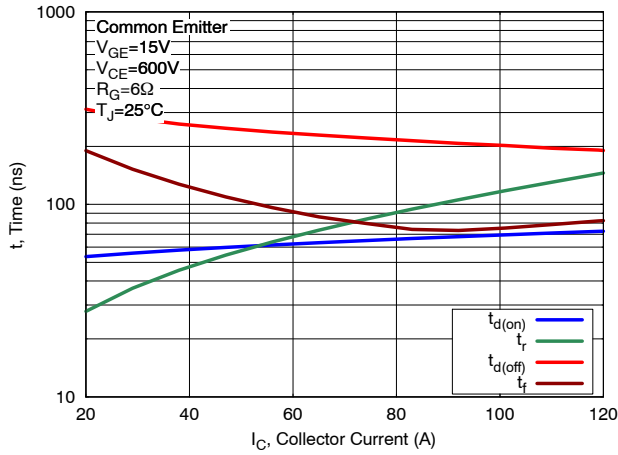


Figure 13. Switching Time vs Collector Current

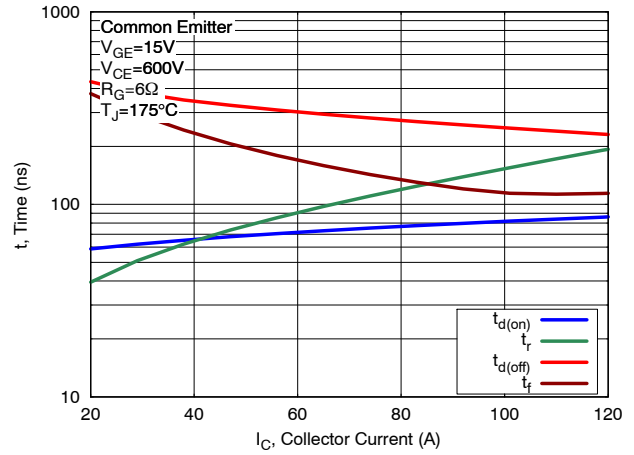


Figure 14. Switching Time vs Collector Current

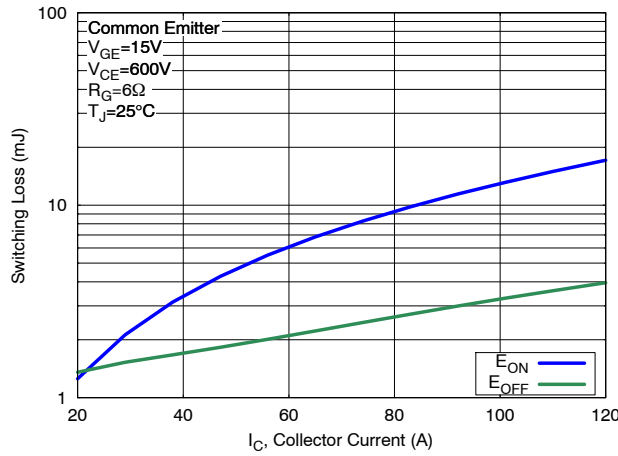


Figure 15. Switching Loss vs Collector Current

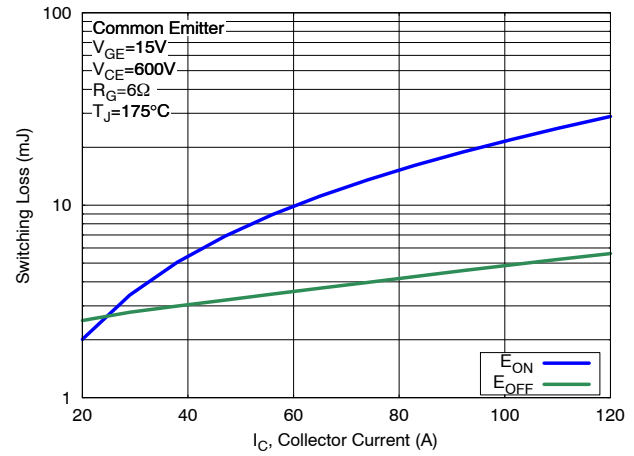


Figure 16. Switching Loss vs Collector Current

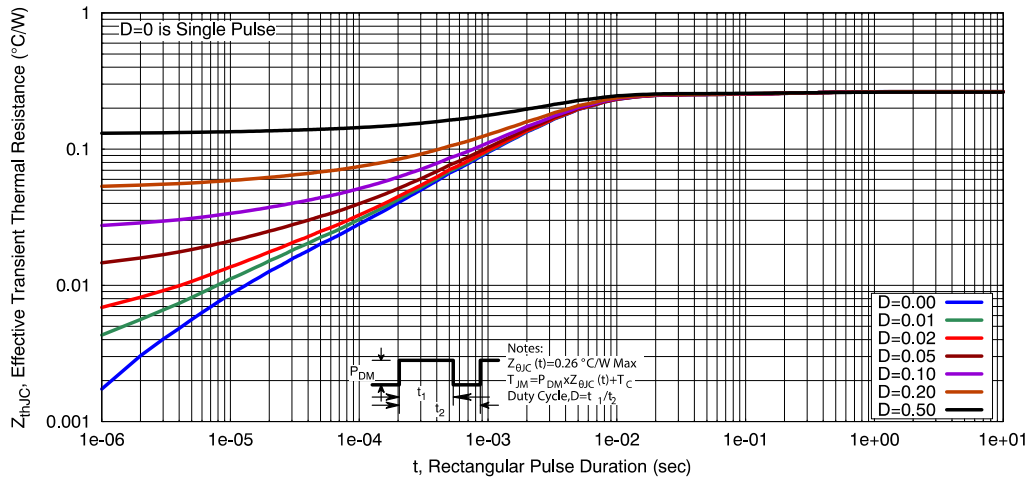


Figure 17. Transient Thermal Impedance of IGBT

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-4LD
CASE 340CJ
ISSUE A

DATE 16 SEP 2019



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.10	2.40	2.70
A2	1.80	2.00	2.20
b	1.07	1.20	1.33
b1	1.20	1.40	1.60
b2	2.02	2.22	2.42
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.25	16.50
D2	0.97	1.17	1.37
e	2.54 BSC		
e1	5.08 BSC		
E	15.40	15.60	15.80
E1	12.80	13.00	13.20
E/2	4.80	5.00	5.20
L	18.22	18.42	18.62
L1	2.42	2.62	2.82
p	3.40	3.60	3.80
p1	6.60	6.80	7.00
Q	5.97	6.17	6.37
S	5.97	6.17	6.37

NOTES:

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